

### Abstract of the Disclosure

A semiconductor device having bonding pads on a semiconductor substrate includes: an upper copper layer that is formed on the lower surface of the bonding pads with a barrier metal interposed and that has a copper area ratio that is greater than layers in which circuit interconnects are  
5 formed; and a lower copper layer that is electrically insulated from the upper copper layer and that is formed closer to the semiconductor substrate than the upper copper layer.